Electronic Supplementary Material (ESI) for RSC Advances.

Supporting Information

MOF-derived self-sacrificing route to hollow NiS_2/ZnS nanospheres for high performance supercapacitors

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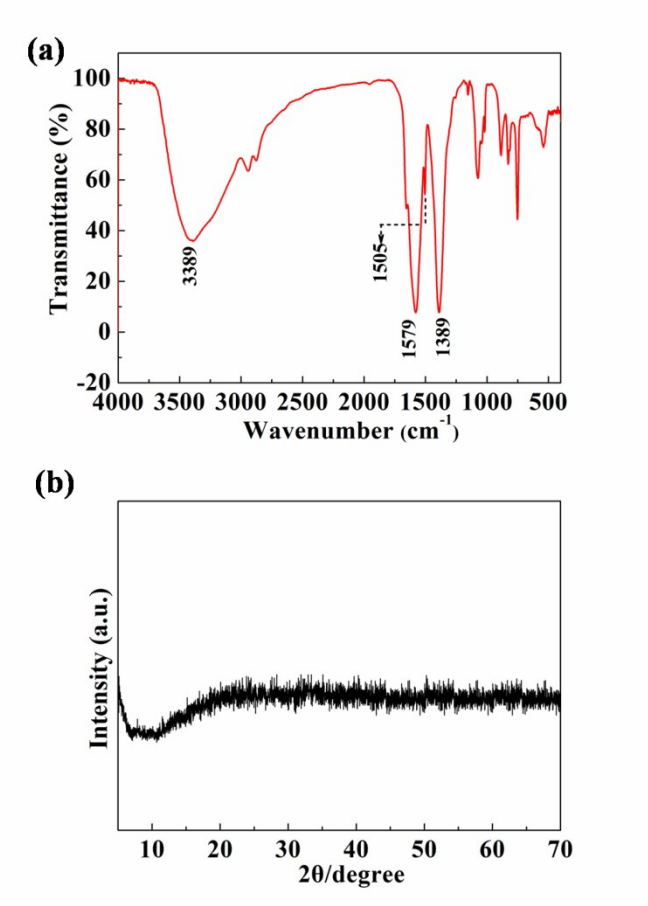

Figure S1. FT-IR spectrum (a) and XRD pattern (b) of the Ni/Zn-BDC MOF spheres.

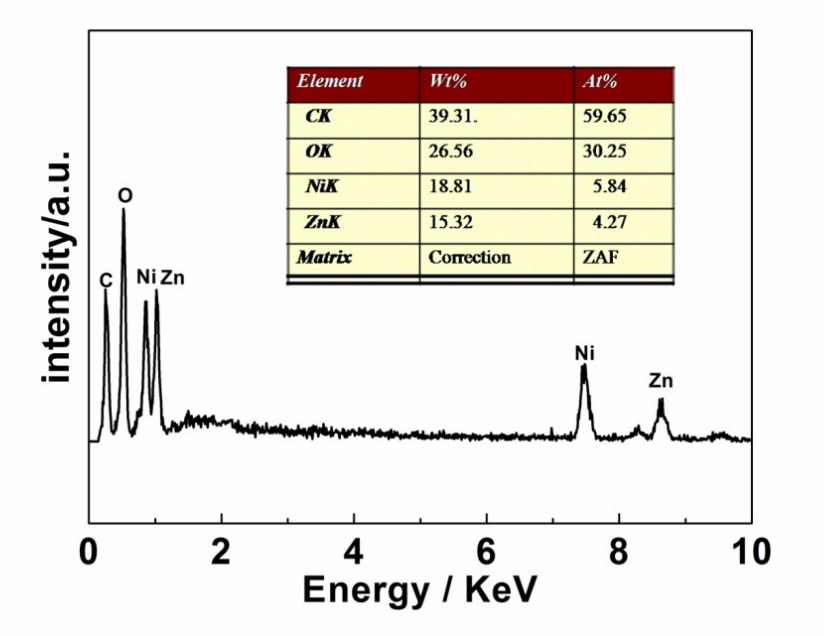

Figure S2. EDS pattern of the Ni/Zn-BDC MOF spheres.

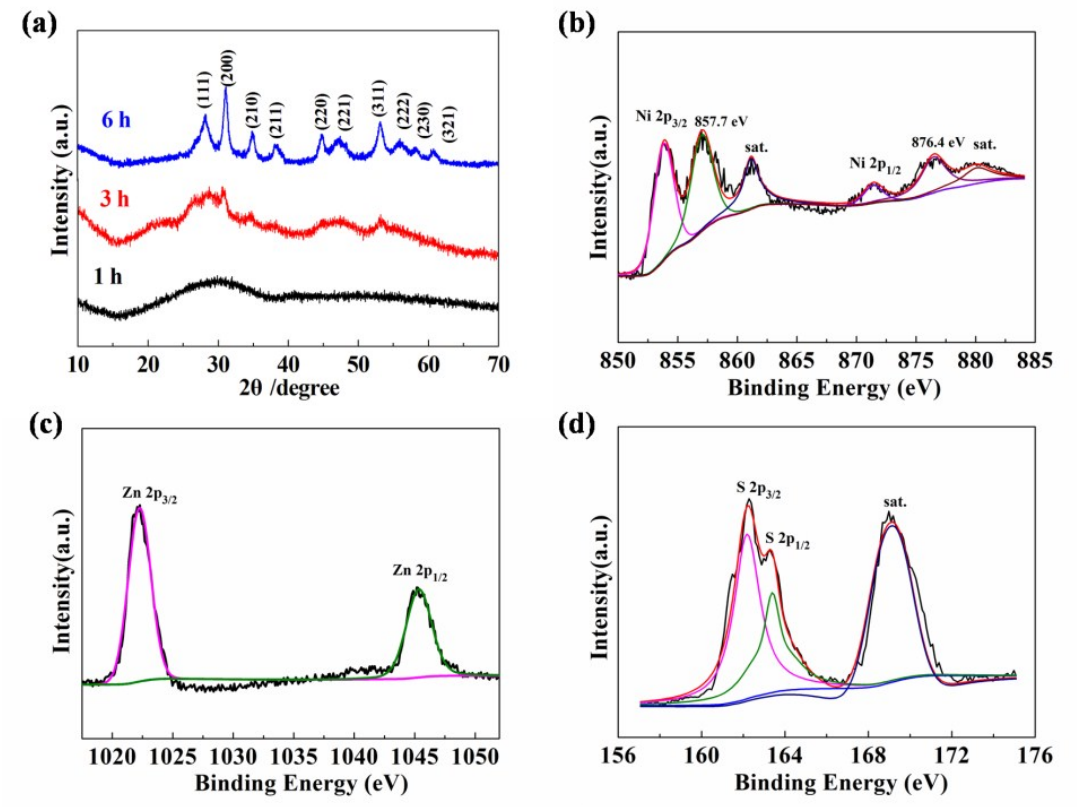

Figure S3. XRD (a) and XPS (b-c) patterns of the NiS_2/ZnS hollow nanospheres

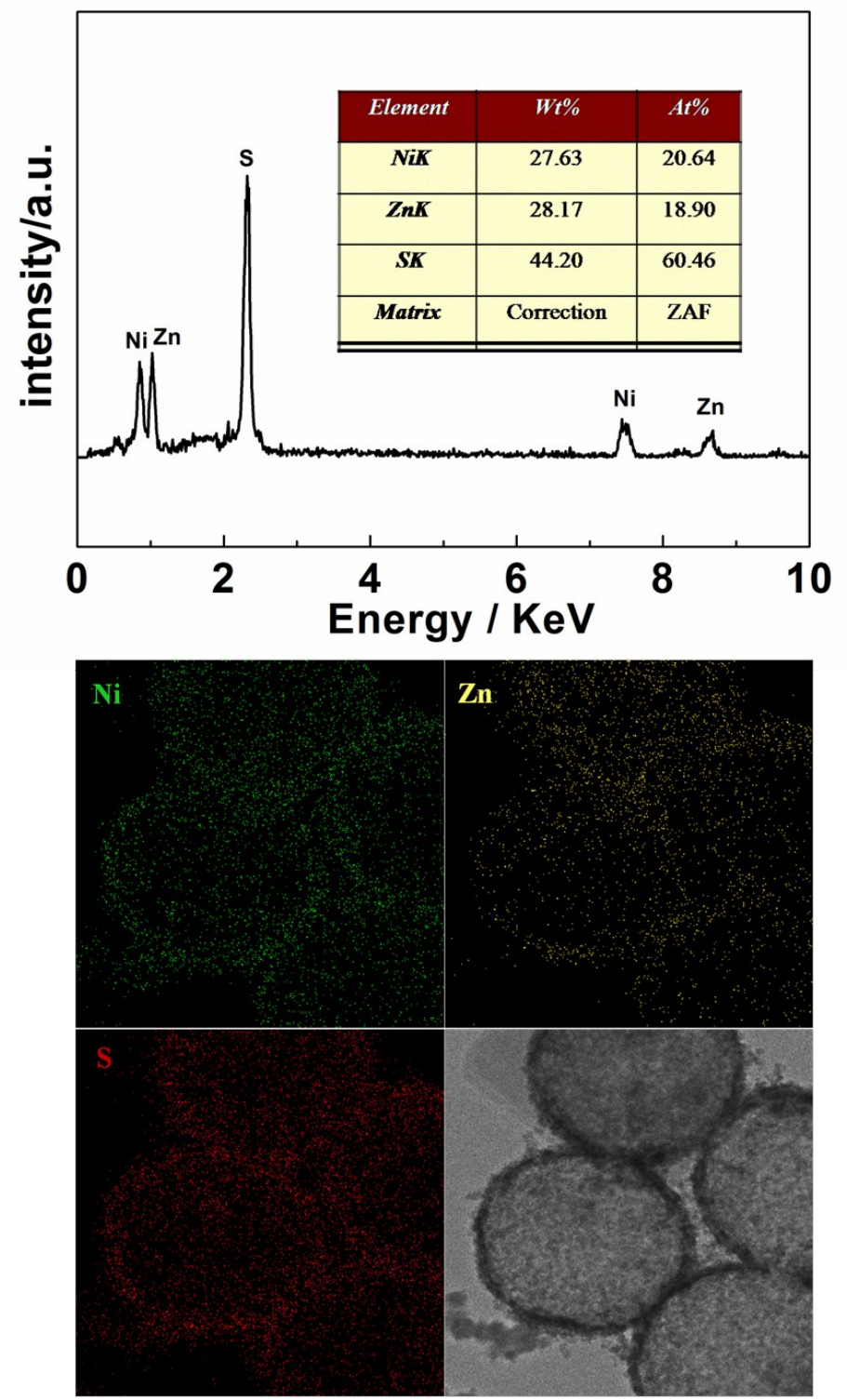

Figure S4. EDS pattern of the NiS_2/ZnS hollow nanospheres.

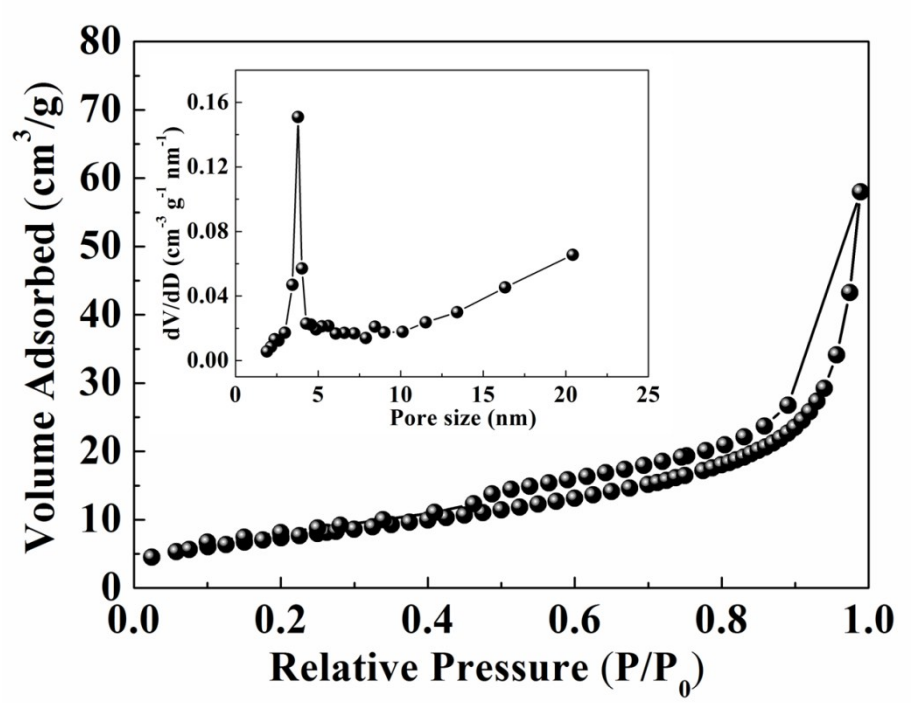

Figure S5. N_2 adsorption-desorption isotherms and pore size distribution (inset) of the NiS_2/ZnS hollow nanospheres.

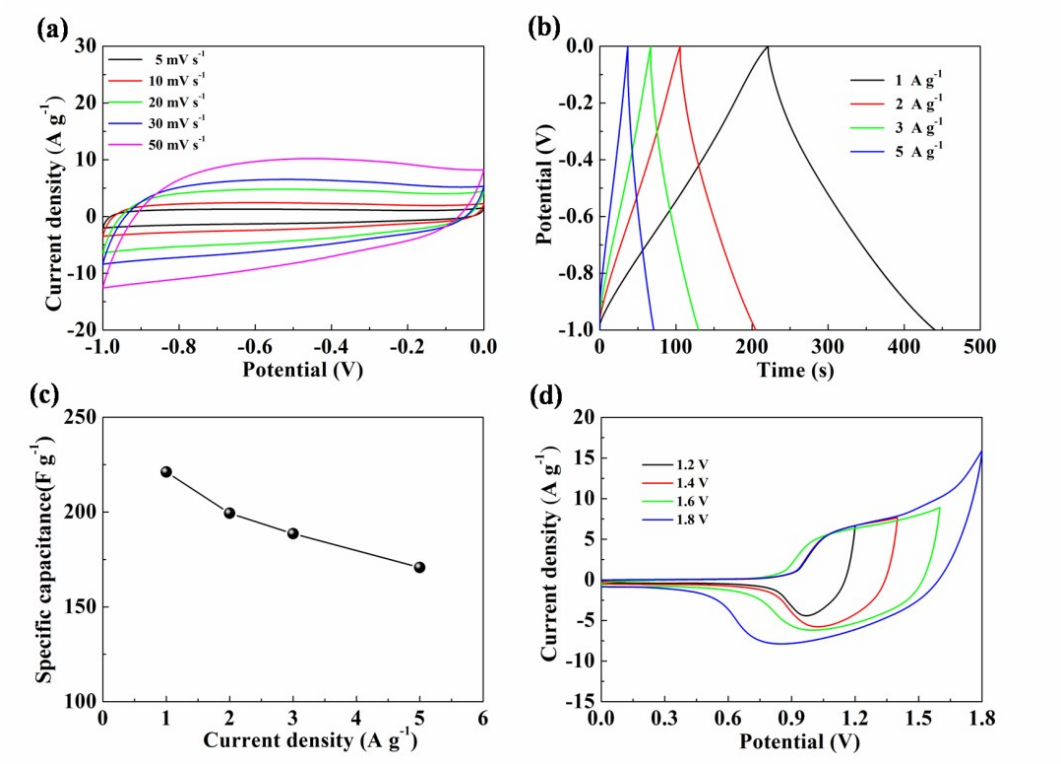

Figure S6. CV curves of AC electrode at different scan rates; (b) GCD curves of AC electrode at different current densities; (c) The corresponding specific capacitance calculated by the GCD curves; (d) CV curves of the ASC at different voltage windows at a scan rate of 30 mV s^{-1}.